28 August 2013

Product data sheet

1. General description

PNP low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

NPN complement: PBSS4260QA.

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C
- High energy efficiency due to less heat generation
- Reduced Printed-Circuit Board (PCB) area requirements
- Solderable side pads
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-60	V
I _C	collector current		-	-	-1.7	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; pulsed	-	-	-2.5	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = -1 A; I_B = -100 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$; T_{amb} = 25 °C	-	195	280	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	Е	emitter		В
3	С	collector	4 3	'`
4	С	collector	2	sym132
			Transparent top view DFN1010D-3 (SOT1215)	

6. Ordering information

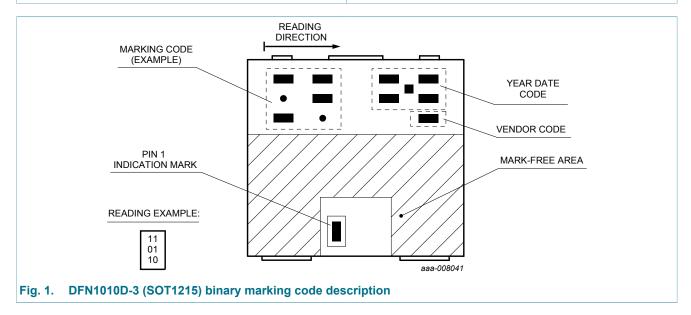
Table 3. Ordering information

Type number	Package	ckage				
	Name	Description	Version			
PBSS5260QA	DFN1010D-3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals	SOT1215			

7. Marking

Table 4. Marking codes

Type number	Marking code
PBSS5260QA	10 00 10



PBSS5260QA

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8. Limiting values

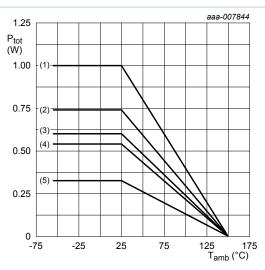
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-60	V
V_{CEO}	collector-emitter voltage	open base		-	-60	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-1.7	Α
I _{CM}	peak collector current	t _p ≤ 1 ms; pulsed		-	-2.5	Α
I _B	base current			-	-0.3	Α
I _{BM}	peak base current	t _p ≤ 1 ms; pulsed		-	-1	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			[5]	-	1000	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

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- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, single-sided copper, 6 cm²
- (3) FR4 PCB, single-sided copper, 1 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient		in free air	[1]	-	-	385	K/W
		[2]	-	-	209	K/W	
	ambient		[3]	-	-	169	K/W
			[4]	-	-	232	K/W
			<u>[5]</u>	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated mounting pad for collector 1 cm².

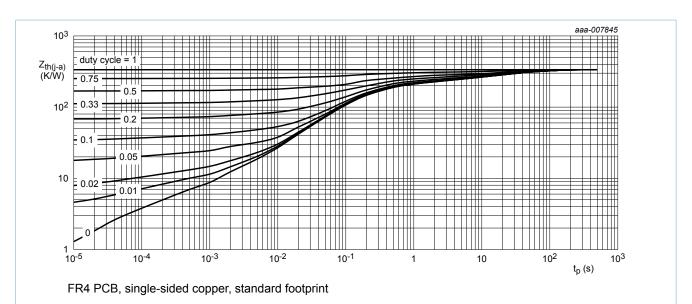


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

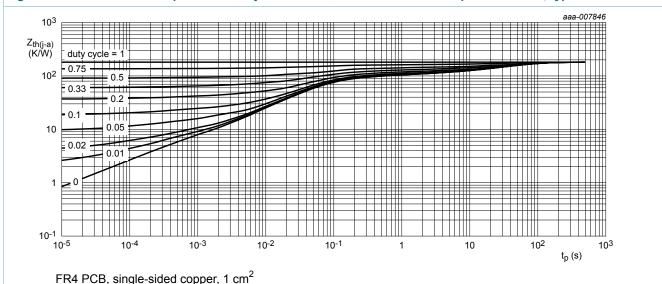


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

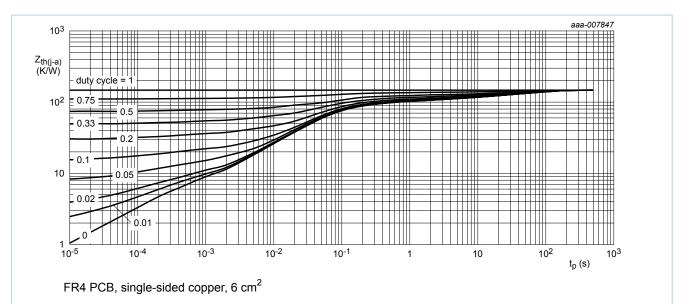


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

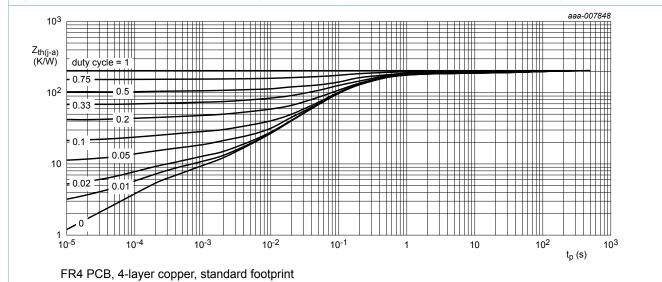
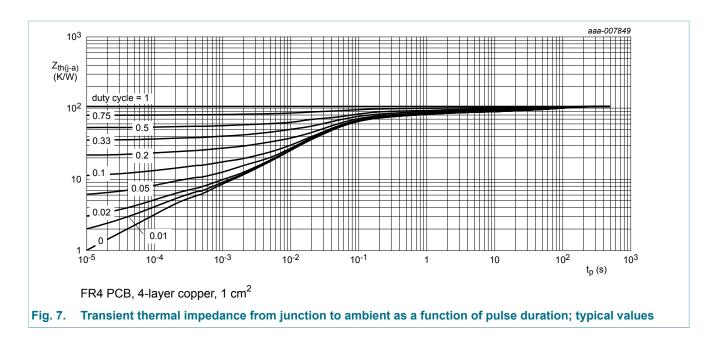


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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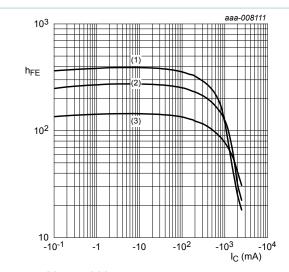


10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = -48 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -48 V; I _E = 0 A; T _j = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V _{CE} = -48 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -2 V; I_{C} = -100 mA; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	160	250	-	
		V_{CE} = -2 V; I_{C} = -500 mA; t_{p} ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	120	185	-	
		V_{CE} = -2 V; I_{C} = -1 A; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C; pulsed	85	125	-	
		V_{CE} = -2 V; I_{C} = -1.7 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	30	45	-	
V _{CEsat}	collector-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; t_{p} ≤ 300 µs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-105	-155	mV
		I_C = -1 A; I_B = -50 mA; t_p ≤ 300 μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-280	-400	mV
		I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb} = 25 \ ^{\circ}C$	-	-195	-280	mV

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		I_{C} = -1.3 A; I_{B} = -65 mA; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	-	-480	-700	mV
		I_{C} = -1.7 A; I_{B} = -170 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-350	-500	mV
R _{CEsat}	collector-emitter saturation resistance	I_{C} = -1 A; I_{B} = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	195	280	mΩ
DEGAL	base-emitter saturation voltage	I_{C} = -500 mA; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-0.85	-1	V
		I_{C} = -1 A; I_{B} = -50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-0.88	-1.05	V
		I_{C} = -1.3 A; I_{B} = -65 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-0.91	-1.1	V
		I_C = -1.7 A; I_B = -170 mA; pulsed; $t_p \le 300$ μs; δ ≤ 0.02 ; T_{amb} = 25 °C	-	-1	-1.15	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I_{C} = -0.5 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-0.78	-0.9	V
t _d	delay time	V_{CC} = -10 V; I_{C} = -0.5 A; I_{Bon} = -25 mA;	-	15	-	ns
t _r	rise time	I _{Boff} = 25 mA; T _{amb} = 25 °C	-	35	-	ns
t _{on}	turn-on time		-	50	-	ns
t _s	storage time		-	300	-	ns
t _f	fall time		-	50	-	ns
t _{off}	turn-off time		-	350	-	ns
f _T	transition frequency	V_{CE} = -10 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	100	150	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	12	15	pF



$$V_{CE} = -2 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55$$
 °C

Fig. 8. DC current gain as a function of collector current; typical values

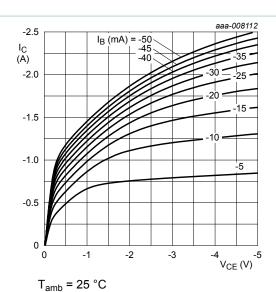
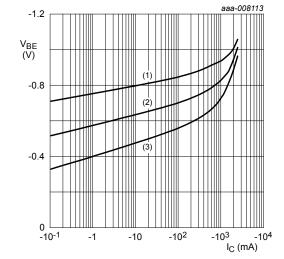


Fig. 9. Collector current as a function of collectoremitter voltage; typical values



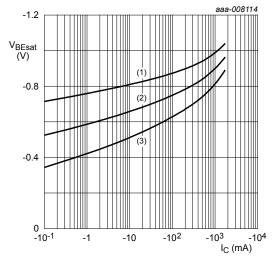
$$V_{CE} = -2 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 10. Base-emitter voltage as a function of collector current; typical values



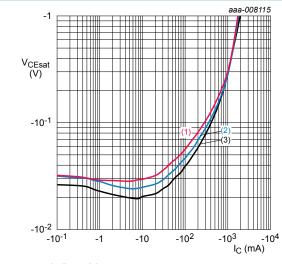
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. Base-emitter saturation voltage as a function of collector current; typical values



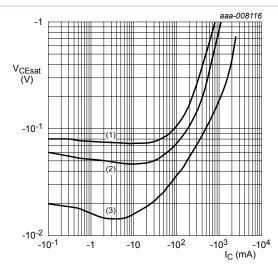
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



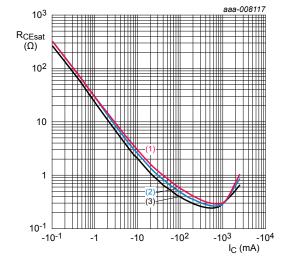
$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 13. Collector-emitter saturation voltage as a function of collector current; typical values

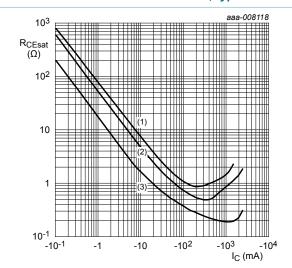


(1)
$$I_C/I_B = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

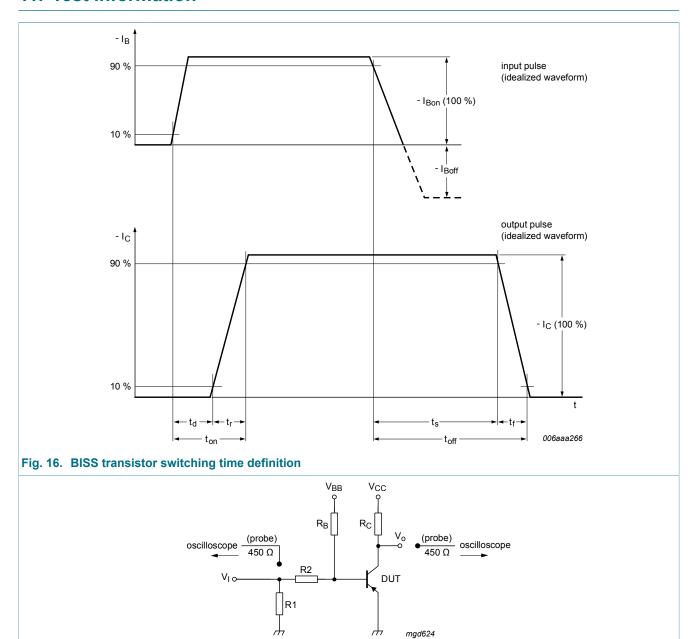
(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 15. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information



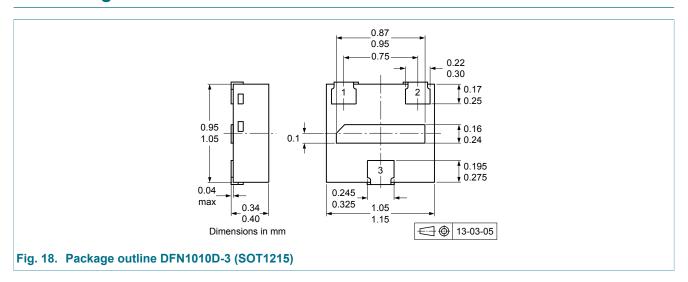
11.1 Quality information

Fig. 17. Test circuit for switching times

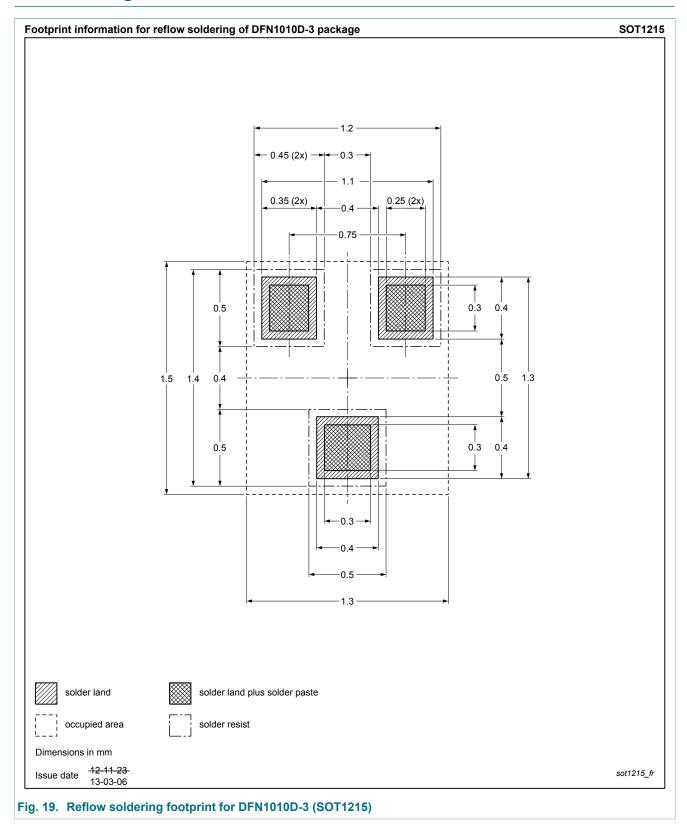
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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12. Package outline



13. Soldering



PBSS5260QA

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5260QA v.1	20130828	Product data sheet	-	-

60 V, 1.7 A PNP low VCEsat (BISS) transistor

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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